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(54) **Title:** METHOD FOR FORMING GATE STRUCTURES

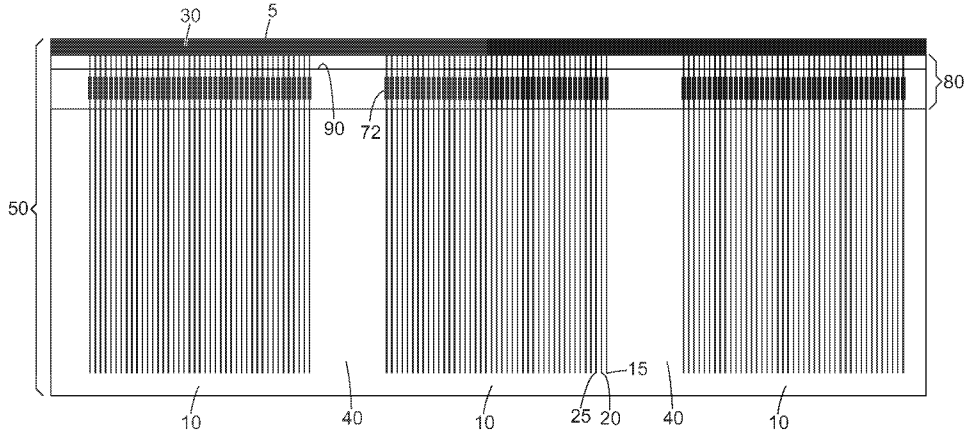


Fig. 1

(57) **Abstract:** A process for forming gate structures is described. A web comprises a substrate, a plurality of conductive elements disposed on the substrate, and a conductive anodization bus. The web is moved through an anodization station to form a plurality of gate structures comprising a plurality of gate dielectrics adjacent to a plurality of gate electrodes. A process for forming electronic devices further providing a semiconductor, a source electrode, and a drain electrode is described.

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